1 A very low V<sub>F</sub> MEGA Schottky barrier rectifiers

Rev. 03 — 28 March 2007

Pro

**Product data sheet** 

## **Product profile**

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview** 

Type number	Package		Configuration
	NXP	JEITA	
PMEG2010AEH	SOD123F	-	single
PMEG2010AET	SOT23	-	single

#### 1.2 Features

Forward current: I<sub>F</sub> ≤ 1 A

Reverse voltage: V<sub>R</sub> ≤ 20 V

Very low forward voltage

Small SMD plastic packages

#### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

Table 2. **Quick reference data** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current	$T_{sp} \le 55  ^{\circ}C$	-	-	1	Α
$V_R$	reverse voltage		-	-	20	V
$V_{F}$	forward voltage	I <sub>F</sub> = 1 A	<u>[1]</u> _	380	430	mV

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



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## 2. Pinning information

Table 3. Pinning

Table J.	i iiiiiiig		
Pin	Description	Simplified outline	Symbol
SOD123F			
1	cathode	[1]	. 84
2	anode	1 2	1 🔀 2
			sym001
SOT23			
1	anode		_
2	not connected	3	3
3	cathode		1 - 2 n.c.
		1 2	006aaa436

<sup>[1]</sup> The marking bar indicates the cathode.

## 3. Ordering information

Table 4. Ordering information

Type number	Package			
	Name	Description	Version	
PMEG2010AEH	-	plastic surface-mounted package; 2 leads	SOD123F	
PMEG2010AET	-	plastic surface-mounted package; 3 leads	SOT23	

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PMEG2010AEH	AF
PMEG2010AET	*AX

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

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## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage		-	20	V
I <sub>F</sub>	forward current	$T_{sp} \le 55  ^{\circ}C$	-	1	Α
I <sub>FRM</sub>	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$			
	PMEG2010AEH		-	7	Α
	PMEG2010AET		-	6	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	-	9	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PMEG2010AEH		[1] _	375	mW
			[2] _	830	mW
	PMEG2010AET		[1] -	280	mW
			[2] _	420	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PMEG2010AEH		[2] _	-	330	K/W
			[3]	-	150	K/W
	PMEG2010AET		[2] _	-	440	K/W
			[3]	-	300	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[4]			
	PMEG2010AEH		-	-	60	K/W
	PMEG2010AET		-	-	120	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

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<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[4]</sup> Soldering point of cathode tab.

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## 7. Characteristics

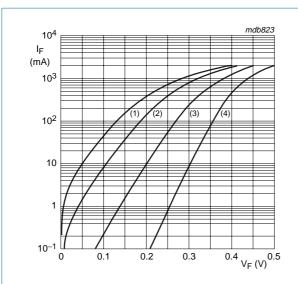
Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub> forward voltage			<u>[1]</u>			
	I <sub>F</sub> = 10 mA	-	200	220	mV	
		I <sub>F</sub> = 100 mA	-	265	290	mV
		I <sub>F</sub> = 1 A	-	380	430	mV
I <sub>R</sub> reverse current	$V_R = 5 V$	-	15	50	μΑ	
	V <sub>R</sub> = 10 V	-	20	80	μΑ	
		V <sub>R</sub> = 20 V	-	50	200	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 5 V$ ; $f = 1 MHz$	-	55	70	pF

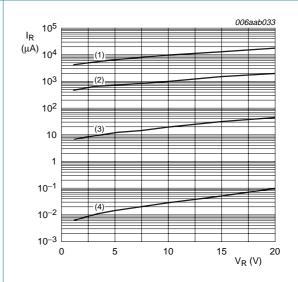
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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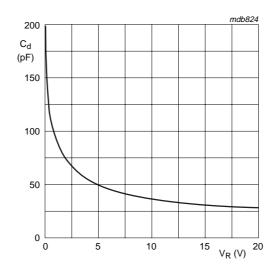
- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values



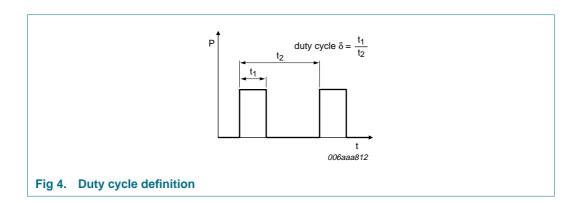
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 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ 

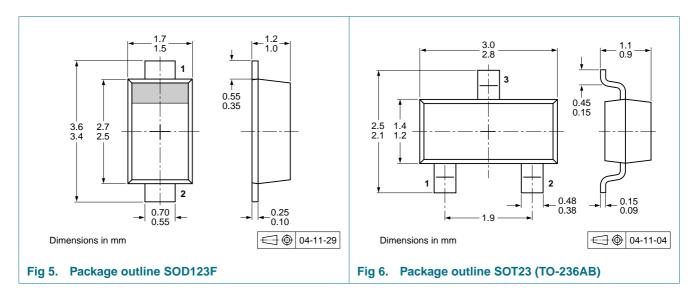
Fig 3. Diode capacitance as a function of reverse voltage; typical values

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### 8. Test information



## 9. Package outline



## 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

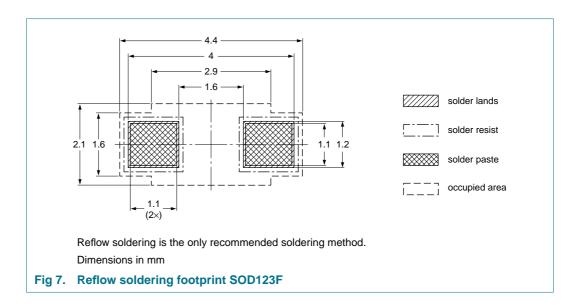
Type number	Package	Description	Packing q	uantity
			3000	10000
PMEG2010AEH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135
PMEG2010AET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

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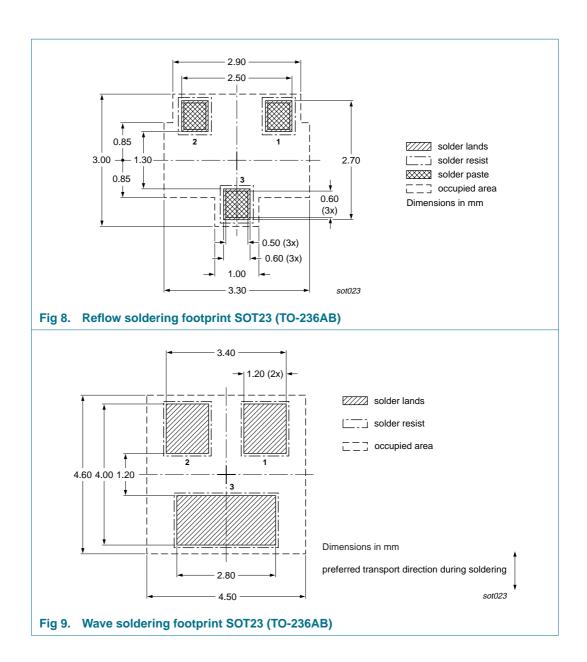
[1] For further information and the availability of packing methods, see Section 14.

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## 11. Soldering



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## 12. Revision history

### Table 10. Revision history

_				
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2010AEH_PMEG2010AET_3	20070328	Product data sheet	-	PMEG2010AEH_2
Modifications:		f this data sheet has bee	· ·	ply with the new
	<ul> <li>Legal texts have</li> </ul>	ave been adapted to the	new company name	where appropriate.
	<ul> <li>Type number</li> </ul>	PMEG2010AET added		
	• Section 1.1 "	General description": am	ended	
	• Table 1 "Proc	duct overview": added		
	• Table 7 "Ther	rmal characteristics": Tab	ole note 1 amended	
	• Table 7 "Ther	rmal characteristics": Tab	ole note 4 added	
	• Table 8 "Cha	racteristics": C <sub>d</sub> diode ca	pacitance conditions	adapted
	• Figure 2: am	ended		
	Section 8 "Te	est information": added		
	Section 13 "L	<u>egal information"</u> : updat	ed	
PMEG2010AEH_2	20050526	Product data sheet	-	PMEG2010AEH_1
PMEG2010AEH_1	20050406	Product data sheet	-	-

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### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### **NXP Semiconductors**

# PMEG2010AEH; PMEG2010AET

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